



ISP1102

Advanced Universal Serial Bus transceiver

Rev. 02 — 06 January 2003

Product data

1. General description

The ISP1102 Universal Serial Bus (USB) transceiver is fully compliant with the *Universal Serial Bus Specification Rev. 2.0*. The ISP1102 can transmit and receive USB data at full-speed (12 Mbit/s).

The transceiver allows USB Application Specific ICs (ASICs) and Programmable Logic Devices (PLDs) with power supply voltages from 1.65 to 3.6 V to interface with the physical layer of the USB. The transceiver has an integrated 5 V-to-3.3 V voltage regulator for direct powering via the USB supply line V_{BUS} . The transceiver has an integrated voltage detector to detect the presence of the V_{BUS} voltage ($V_{CC(5.0)}$). When $V_{CC(5.0)}$ or $V_{reg(3.3)}$ is lost, the D+ and D- pins can be shared with other serial protocols.

The transceiver is a bi-directional differential interface and is available in the HBCC16 package.

The transceiver is ideal for use in portable electronic devices, such as mobile phones, digital still cameras, personal digital assistants and information appliances.

2. Features

- Complies with *Universal Serial Bus Specification Rev. 2.0*
- Supports data transfer at full-speed (12 Mbit/s)
- Integrated 5 V-to-3.3 V voltage regulator for powering via USB line V_{BUS}
- V_{BUS} voltage presence indication on pin VBUSDET
- VP and VM pins function in bi-directional mode allowing pin count saving for ASIC interface
- Used as USB device transceiver or USB host transceiver
- Stable RCV output during single-ended zero (SE0) condition
- Two single-ended receivers with hysteresis
- Low-power operation
- Supports I/O voltage range from 1.65 to 3.6 V
- ± 12 kV ESD protection at D+, D-, $V_{CC(5.0)}$ and GND pins
- Full industrial operating temperature range from -40 to $+85$ C
- Available in HBCC16 package.



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3. Applications

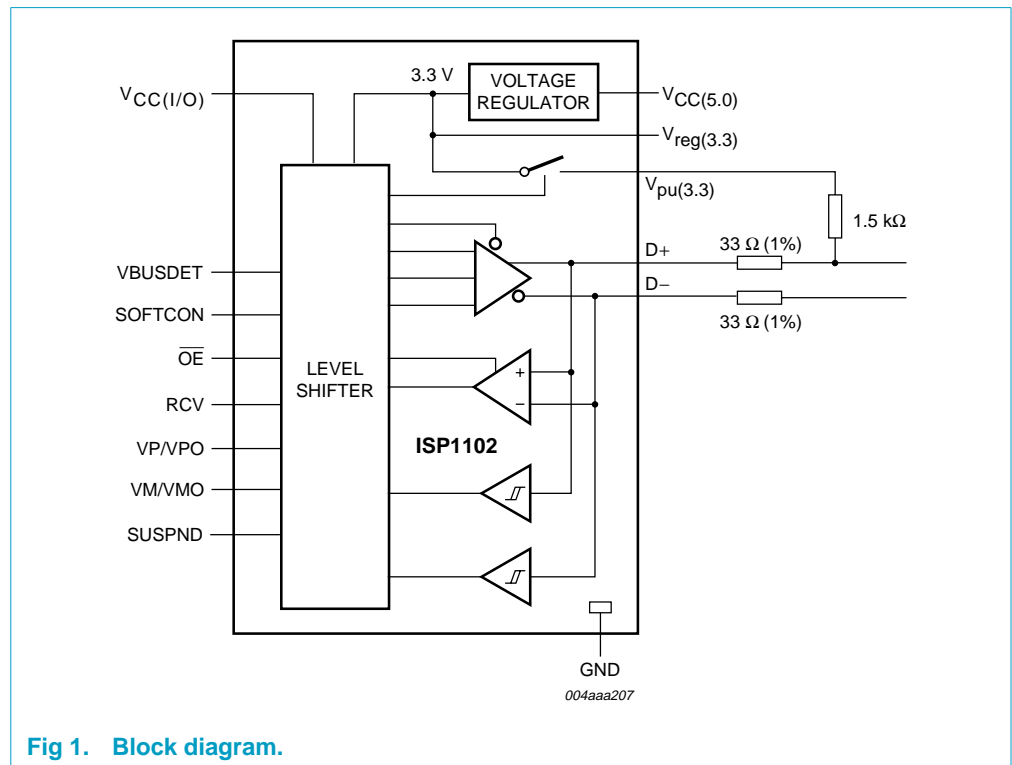
- Portable electronic devices, such as:
 - ◆ Mobile phone
 - ◆ Digital Still Camera (DSC)
 - ◆ Personal Digital Assistant (PDA)
 - ◆ Information Appliance (IA).

4. Ordering information

Table 1: Ordering information

Type number	Package		Version
	Name	Description	
ISP1102W	HBCC16	plastic thermal enhanced bottom chip carrier; 16 terminals; body 3 × 3 × 0.65 mm	SOT639-2

5. Block diagram



6. Pinning information

6.1 Pinning

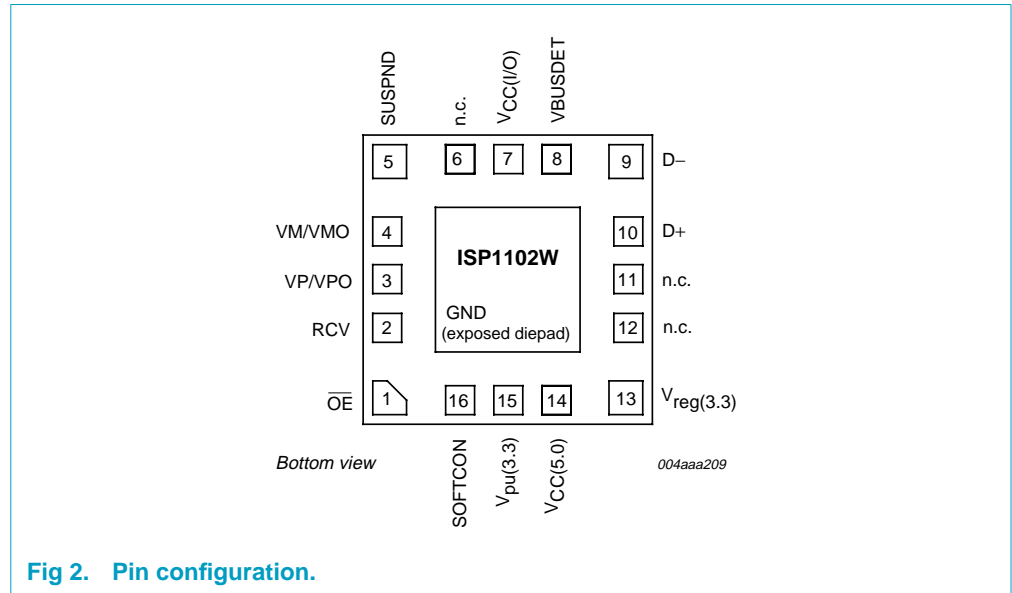


Fig 2. Pin configuration.

6.2 Pin description

Table 2: Pin description

Symbol ^[1]	Pin	Type	Description
$\overline{\text{OE}}$	1	I	input for output enable (CMOS level with respect to $V_{\text{CC(I/O)}}$, active LOW); enables the transceiver to transmit data on the USB bus
RCV	2	O	differential data receiver output (CMOS level with respect to $V_{\text{CC(I/O)}}$); driven LOW when input SUSPND is HIGH; the output state of RCV is preserved and stable during an SE0 condition
VP/VPO	3	I/O	single-ended D+ receiver output VP (CMOS level with respect to $V_{\text{CC(I/O)}}$); for external detection of SE0, error conditions, speed of connected device; this pin also acts as the drive data input VPO; see Table 3 and Table 4
VM/VMO	4	I/O	single-ended D- receiver output VM (CMOS level with respect to $V_{\text{CC(I/O)}}$); for external detection of SE0, error conditions, speed of connected device; this pin also acts as the drive data input VMO; see Table 3 and Table 4
SUSPND	5	I	suspend input (CMOS level with respect to $V_{\text{CC(I/O)}}$); a HIGH level enables low-power state while the USB bus is inactive and drives output RCV to a LOW level
n.c.	6	-	not connected
$V_{\text{CC(I/O)}}$	7	-	supply voltage for digital I/O pins (1.65 to 3.6 V). When $V_{\text{CC(I/O)}}$ is not connected, the D+ and D- pins are in three-state. This supply pin is totally independent of $V_{\text{CC(5.0)}}$ and $V_{\text{reg(3.3)}}$ and must never exceed the $V_{\text{reg(3.3)}}$ voltage.

Table 2: Pin description...continued

Symbol ^[1]	Pin	Type	Description
VBUSDET	8	O	V _{BUS} indicator output (CMOS level with respect to V _{CC(I/O)}); when V _{BUS} > 4.1 V, then VBUSDET = HIGH and when V _{BUS} < 3.6 V, then VBUSDET = LOW; when SUSPND = HIGH, then pin VBUSDET is pulled HIGH
D-	9	AI/O	negative USB data bus connection (analog, differential)
D+	10	AI/O	positive USB data bus connection (analog, differential)
n.c.	11		not connected
n.c.	12		not connected
V _{reg(3.3)}	13	-	internal regulator option: regulated supply voltage output (3.0 to 3.6 V) during 5 V operation; a decoupling capacitor of at least 0.1 μF is required regulator bypass option: used as a supply voltage input (3.3 V ±10%) for 3.3 V operation
V _{CC(5.0)}	14	-	internal regulator option: supply voltage input (4.0 to 5.5 V); can be connected directly to USB line V _{BUS} regulator bypass option: connect to V _{reg(3.3)}
V _{pu(3.3)}	15	-	pull-up supply voltage (3.3 V ±10%); connect an external 1.5 kΩ resistor on D+ (full-speed). Pin function is controlled by input SOFTCON: SOFTCON = LOW — V _{pu(3.3)} floating (high impedance); ensures zero pull-up current SOFTCON = HIGH — V _{pu(3.3)} = 3.3 V; internally connected to V _{reg(3.3)}
SOFTCON	16	I	software controlled USB connection input; a HIGH level applies 3.3 V to pin V _{pu(3.3)} , which is connected to an external 1.5 kΩ pull-up resistor; this allows USB connect or disconnect signalling to be controlled by software
GND	exposed die pad	-	ground supply; down bonded to the exposed die pad (heatsink); to be connected to the PCB ground

[1] Symbol names with an overscore (e.g. \overline{OE}) indicate active LOW signals.

7. Functional description

7.1 Function selection

Table 3: Function table

SUSPND	\overline{OE}	D+, D–	RCV	VP/VPO	VM/VMO	Function
L	L	driving and receiving	active	VPO input	VMO input	normal driving (differential receiver active)
L	H	receiving ^[1]	active	VP output	VM output	receiving
H	L	driving	inactive ^[2]	VPO input	VMO input	driving during suspend (differential receiver inactive)
H	H	high-Z ^[1]	inactive ^[2]	VP output	VM output	low-power state

- [1] Signal levels on the D+ and D– pins are determined by other USB devices and external pull-up or pull-down resistors.
- [2] In the suspend mode (SUSPND = HIGH), the differential receiver is inactive and the output RCV is always LOW. Out-of-suspend (K) signalling is detected via the single-ended receivers VP/VPO and VM/VMO.

7.2 Operating functions

Table 4: Driving function using differential input data interface (pin $\overline{OE} = L$)

VM/VMO	VP/VPO	Data
L	L	SE0
L	H	differential logic 1
H	L	differential logic 0
H	H	illegal state

Table 5: Receiving function (pin $\overline{OE} = H$)

D+, D–	RCV	VP/VPO	VM/VMO
differential logic 0	L	L	H
differential logic 1	H	H	L
SE0	RCV* ^[1]	L	L

- [1] RCV* denotes the signal level on output RCV just before the SE0 state occurs. This level is stable during the SE0 period.

7.3 Power supply configurations

The ISP1102 can be used with different power supply configurations, which can be changed dynamically. Table 7 provides an overview of the power supply configurations.

Normal mode — $V_{CC(I/O)}$ and $V_{CC(5.0)}$ are connected or $V_{CC(5.0)}$ and $V_{reg(3.3)}$ are connected.

For 5 V operation, $V_{CC(5.0)}$ is connected to a 5 V source (4.0 to 5.5 V). The internal voltage regulator then produces 3.3 V for the USB connections.

For 3.3 V operation, both $V_{CC(5.0)}$ and $V_{reg(3.3)}$ are connected to a 3.3 V source (3.0 to 3.6 V).

$V_{CC(I/O)}$ is independently connected to a voltage source (1.65 to 3.6 V), depending on the supply voltage of the external circuit.

Sharing mode — $V_{CC(I/O)}$ is connected only; $V_{CC(5.0)}$ and $V_{reg(3.3)}$ are not connected. In this mode, the D+ and D– pins are made three-state and the ISP1102 allows external signals of up to 3.6 V to share the D+ and D– lines. The internal circuits of the ISP1102 ensure that virtually no current (maximum 10 μ A) is drawn via the D+ and D– lines. The power consumption through pin $V_{CC(I/O)}$ drops to the low-power (suspended) state level.

Pins VBUSDET and RCV are driven LOW to indicate this mode. The VBUSDET function is ignored during the suspend mode of the ISP1102.

Some hysteresis is built into the detection of $V_{reg(3.3)}$ lost.

Table 6: Pin states in the sharing mode

Pin	Sharing mode
$V_{CC(5.0)}$	not present
$V_{reg(3.3)}$	not present
$V_{CC(I/O)}$	1.65 to 3.6 V input
$V_{pu(3.3)}$	high impedance (off)
D+, D–	high impedance
VP/VPO, VM/VMO	L
RCV	L
VBUSDET	L
\overline{OE} , SUSPND, SOFTCON	high impedance

Table 7: Power supply configuration overview

$V_{CC(5.0)}$	Configuration	Special characteristics
connected	normal mode	-
not connected	sharing mode	D+, D– and $V_{pu(3.3)}$ high impedance; VBUSDET driven LOW

7.4 Power supply input options

The ISP1102 has two power supply input options:

Internal regulator — pin $V_{CC(5.0)}$ is connected to 4.0 to 5.5 V. The internal regulator is used to supply the internal circuitry with 3.3 V (nominal). The $V_{reg(3.3)}$ pin becomes a 3.3 V output reference.

Regulator bypass — pins $V_{CC(5.0)}$ and $V_{reg(3.3)}$ are connected to the same supply. The internal regulator is bypassed and the internal circuitry is supplied directly from pin $V_{reg(3.3)}$. The voltage range is 3.0 to 3.6 V to comply with the USB specification.

The supply voltage range for each input option is specified in [Table 8](#).

Table 8: Power supply input options

Input option	$V_{CC(5.0)}$	$V_{reg(3.3)}$	$V_{CC(I/O)}$
Internal regulator	supply input for internal regulator (4.0 to 5.5 V)	voltage reference output (3.3 V, 300 μ A)	supply input for digital I/O pins (1.65 V to 3.6 V)
Regulator bypass	connected to $V_{reg(3.3)}$ with maximum voltage drop of 0.3 V (2.7 to 3.6 V)	supply input (3.0 V to 3.6 V)	supply input for digital I/O pins (1.65 V to 3.6 V)

8. Electrostatic discharge (ESD)

8.1 ESD protection

The pins that are connected to the USB connector (D+, D-, $V_{CC(5.0)}$ and GND) have a minimum of ± 12 kV ESD protection. The ± 12 kV measurement is limited by the test equipment. Capacitors of $4.7 \mu\text{F}$ connected from $V_{\text{reg}(3.3)}$ to GND and $V_{CC(5.0)}$ to GND are required to achieve this ± 12 kV ESD protection (see Figure 3).

The ISP1102 can withstand ± 12 kV using the Human Body Model and ± 5 kV using the Contact Discharge Method as specified in IEC 61000-4-2.

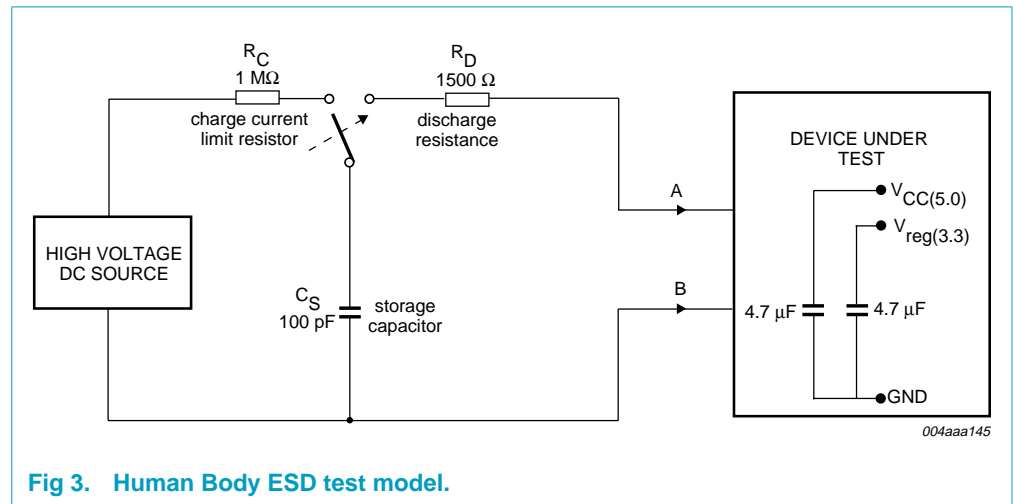


Fig 3. Human Body ESD test model.

8.2 ESD test conditions

A detailed report on test set-up and results is available on request.

9. Limiting values

Table 9: Absolute maximum ratings

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(5.0)}$	supply voltage		-0.5	+6.0	V
$V_{CC(I/O)}$	I/O supply voltage		-0.5	+4.6	V
V_I	DC input voltage		-0.5	$V_{CC(I/O)} + 0.5$	V
I_{lu}	latch-up current	$V_I = -1.8$ to $+5.4$ V	-	100	mA
V_{esd}	electrostatic discharge voltage	pins D+, D-, $V_{CC(5.0)}$ and GND; $I_{LI} < 3 \mu\text{A}$	[1] -12000	+12000	V
		all other pins; $I_{LI} < 1 \mu\text{A}$	-2000	+2000	V
T_{stg}	storage temperature		-40	+125	°C

[1] Testing equipment limits measurement to only ± 12 kV. Capacitors needed on $V_{CC(5.0)}$ and $V_{reg(3.3)}$ (see Section 8).

10. Recommended operating conditions

Table 10: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC(5.0)}$	supply voltage		4.0	5.0	5.5	V
$V_{CC(I/O)}$	I/O supply voltage		1.65	-	3.6	V
V_I	input voltage		0	-	$V_{CC(I/O)}$	V
$V_{I(AI/O)}$	input voltage on AI/O pins	pins D+ and D-	0	-	3.6	V
T_{amb}	ambient temperature		-40	-	+85	°C

11. Static characteristics

Table 11: Static characteristics: supply pins

$V_{CC(5.0)} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; see Table 8 for valid voltage level combinations; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{reg(3.3)}$	regulated supply voltage output	internal regulator option; $I_{load} \leq 300 \mu\text{A}$	[1][2] 3.0	3.3	3.6	V
I_{CC}	operating supply current	transmitting and receiving at 12 Mbit/s; $C_L = 50$ pF on pins D+ and D-	[3] -	4	8	mA
$I_{CC(I/O)}$	operating I/O supply current	transmitting and receiving at 12 Mbit/s	[3] -	1	2	mA
$I_{CC(idle)}$	supply current during full-speed idle and SE0	idle: $V_{D+} > 2.7$ V, $V_{D-} < 0.3$ V; SE0: $V_{D+} < 0.3$ V, $V_{D-} < 0.3$ V	[4] -	-	300	μA
$I_{CC(I/O)(static)}$	static I/O supply current	idle, SE0 or suspend	-	-	20	μA
$I_{CC(susp)}$	suspend supply current	SUSPND = HIGH	[4] -	-	20	μA
$I_{CC(I/O)(sharing)}$	sharing mode I/O supply current	$V_{CC(5.0)}$ not connected	-	-	20	μA

Table 11: Static characteristics: supply pins...continued

$V_{CC(5.0)} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; see [Table 8](#) for valid voltage level combinations; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{Dx(sharing)}$	sharing mode load current on pins D+ and D-	$V_{CC(5.0)}$ not connected; SOFTCON = LOW; $V_{Dx} = 3.6$ V	-	-	10	µA
$V_{CC(5.0)th}$	supply voltage detection threshold	1.65 V $\leq V_{CC(I/O)} \leq 3.6$ V				
		supply lost	-	-	3.6	V
		supply present	4.1	-	-	V
$V_{CC(5.0)hys}$	supply voltage detection hysteresis	$V_{CC(I/O)} = 1.8$ V	-	70	-	mV
$V_{CC(I/O)th}$	I/O supply voltage detection threshold	$V_{reg(3.3)} = 2.7$ to 3.6 V				
		supply lost	-	-	0.5	V
		supply present	1.4	-	-	V
$V_{CC(I/O)hys}$	I/O supply voltage detection hysteresis	$V_{reg(3.3)} = 3.3$ V	-	0.45	-	V
$V_{reg(3.3)th}$	regulated supply voltage detection threshold	1.65 V $\leq V_{CC(I/O)} \leq V_{reg(3.3)}$; 2.7 V $\leq V_{reg(3.3)} \leq 3.6$ V				
		supply lost	-	-	0.8	V
		supply present	[5] 2.4	-	-	V
$V_{reg(3.3)hys}$	regulated supply voltage detection hysteresis	$V_{CC(I/O)} = 1.8$ V	-	0.45	-	V

[1] I_{load} includes the pull-up resistor current via pin $V_{pu(3.3)}$.

[2] The minimum voltage is 2.7 V in the suspend mode.

[3] Maximum value characterized only, not tested in production.

[4] Excluding any load current and $V_{pu(3.3)}$ or V_{sw} source current to the 1.5 kΩ and 15 kΩ pull-up and pull-down resistors (200 µA typ.).

[5] When $V_{CC(I/O)} < 2.7$ V, the minimum value for $V_{reg(3.3)th} = 2.0$ V for supply present condition.

Table 12: Static characteristics: digital pins

$V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC(I/O)} = 1.65$ to 3.6 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	$0.3V_{CC(I/O)}$	V
V_{IH}	HIGH-level input voltage		$0.6V_{CC(I/O)}$	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100$ µA	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100$ µA	$V_{CC(I/O)} - 0.15$	-	-	V
		$I_{OH} = 2$ mA	$V_{CC(I/O)} - 0.4$	-	-	V
Leakage current						
I_{LI}	input leakage current		[1] -1	-	+1	µA

Table 12: Static characteristics: digital pins...continued

$V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Capacitance						
C_{IN}	input capacitance	pin to GND	-	-	10	pF
Example 1: $V_{CC(I/O)} = 1.8$ V \pm 0.15 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	0.5	V
V_{IH}	HIGH-level input voltage		1.2	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100$ μ A	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100$ μ A	1.5	-	-	V
		$I_{OH} = 2$ mA	1.25	-	-	V
Example 2: $V_{CC(I/O)} = 2.5$ V \pm 0.2 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	0.7	V
V_{IH}	HIGH-level input voltage		1.7	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100$ μ A	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100$ μ A	2.15	-	-	V
		$I_{OH} = 2$ mA	1.9	-	-	V
Example 3: $V_{CC(I/O)} = 3.3$ V \pm 0.3 V						
Input levels						
V_{IL}	LOW-level input voltage		-	-	0.9	V
V_{IH}	HIGH-level input voltage		2.15	-	-	V
Output levels						
V_{OL}	LOW-level output voltage	$I_{OL} = 100$ μ A	-	-	0.15	V
		$I_{OL} = 2$ mA	-	-	0.4	V
V_{OH}	HIGH-level output voltage	$I_{OH} = 100$ μ A	2.85	-	-	V
		$I_{OH} = 2$ mA	2.6	-	-	V

[1] If $V_{CC(I/O)} \geq V_{reg(3.3)}$, then the leakage current will be higher than the specified value.

Table 13: Static characteristics: analog I/O pins D+ and D-

$V_{CC(5.0)} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{GND} = 0$ V; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Input levels						
Differential receiver						
V_{DI}	differential input sensitivity	$ V_{I(D+)} - V_{I(D-)} $	0.2	-	-	V
V_{CM}	differential common mode voltage	includes V_{DI} range	0.8	-	2.5	V

Table 13: Static characteristics: analog I/O pins D+ and D–...continued

$V_{CC(5.0)} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{GND} = 0$ V; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Single-ended receiver						
V_{IL}	LOW-level input voltage		-	-	0.8	V
V_{IH}	HIGH-level input voltage		2.0	-	-	V
V_{hys}	hysteresis voltage		0.4	-	0.7	V
Output levels						
V_{OL}	LOW-level output voltage	$R_L = 1.5$ k Ω to 3.6 V	-	-	0.3	V
V_{OH}	HIGH-level output voltage	$R_L = 15$ k Ω to GND	[1] 2.8	-	3.6	V
Leakage current						
I_{LZ}	OFF-state leakage current		-1	-	+1	μ A
Capacitance						
C_{IN}	transceiver capacitance	pin to GND	-	-	20	pF
Resistance						
Z_{DRV}	driver output impedance	steady-state drive	[2] 34	39	44	Ω
Z_{INP}	input impedance		10	-	-	M Ω
R_{SW}	internal switch resistance at pin $V_{pu(3.3)}$		-	-	10	Ω
Termination						
V_{TERM}	termination voltage for upstream port pull-up (R_{pu})		[3][4] 3.0	-	3.6	V

[1] $V_{OH(min)} = V_{reg(3.3)} - 0.2$ V.

[2] Includes external resistors of $33 \Omega \pm 1\%$ on both pins D+ and D–.

[3] This voltage is available at pins $V_{reg(3.3)}$ and $V_{pu(3.3)}$.

[4] The minimum voltage is 2.7 V in the suspend mode.

12. Dynamic characteristics

Table 14: Dynamic characteristics: analog I/O pins D+ and D–

$V_{CC(5.0)} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; see [Table 8](#) for valid voltage level combinations; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Driver characteristics						
t_{FR}	rise time	$C_L = 50$ to 125 pF; 10% to 90% of $ V_{OH} - V_{OL} $; see Figure 4	4	-	20	ns
t_{FF}	fall time	$C_L = 50$ to 125 pF; 90% to 10% of $ V_{OH} - V_{OL} $; see Figure 4	4	-	20	ns
FRFM	differential rise/fall time matching (t_{FR}/t_{FF})	excluding the first transition from Idle state	90	-	111.1	%
V_{CRS}	output signal crossover voltage	excluding the first transition from Idle state; see Figure 5	[1] 1.3	-	2.0	V

Table 14: Dynamic characteristics: analog I/O pins D+ and D-...continued

$V_{CC(5.0)} = 4.0$ to 5.5 V or $V_{reg(3.3)} = 3.0$ to 3.6 V; $V_{CC(I/O)} = 1.65$ to 3.6 V; $V_{GND} = 0$ V; see [Table 8](#) for valid voltage level combinations; $T_{amb} = -40$ to $+85$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Driver timing						
$t_{PLH(drv)}$	driver propagation delay (VPO, VMO to D+, D-)	LOW-to-HIGH; see Figure 5 and Figure 8	-	-	18	ns
$t_{PHL(drv)}$	driver propagation delay (VPO, VMO to D+, D-)	HIGH-to-LOW; see Figure 5 and Figure 8	-	-	18	ns
t_{PHZ}	driver disable delay (\overline{OE} to D+, D-)	HIGH-to-OFF; see Figure 6 and Figure 9	-	-	15	ns
t_{PLZ}	driver disable delay (\overline{OE} to D+, D-)	LOW-to-OFF; see Figure 6 and Figure 9	-	-	15	ns
t_{PZH}	driver enable delay (\overline{OE} to D+, D-)	OFF-to-HIGH; see Figure 6 and Figure 9	-	-	15	ns
t_{PZL}	driver enable delay (OE to D+, D-)	OFF-to-LOW; see Figure 6 and Figure 9	-	-	15	ns
Receiver timings						
Differential receiver						
$t_{PLH(rcv)}$	propagation delay (D+, D- to RCV)	LOW-to-HIGH; see Figure 7 and Figure 10	-	-	15	ns
$t_{PHL(rcv)}$	propagation delay (D+, D- to RCV)	HIGH-to-LOW; see Figure 7 and Figure 10	-	-	15	ns
Single-ended receiver						
$t_{PLH(se)}$	propagation delay (D+, D- to VP/VPO, VM/VMO)	LOW-to-HIGH; see Figure 7 and Figure 10	-	-	18	ns
$t_{PHL(se)}$	propagation delay (D+, D- to VP/VPO, VM/VMO)	HIGH-to-LOW; see Figure 7 and Figure 10	-	-	18	ns

[1] Characterized only, not tested. Limits guaranteed by design.

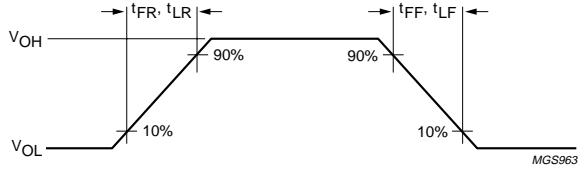


Fig 4. Rise and fall times.

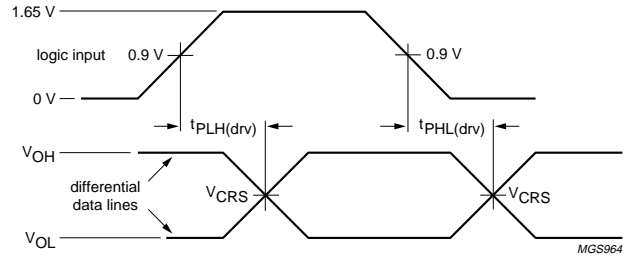


Fig 5. Timing of VPO and VMO to D+ and D-.

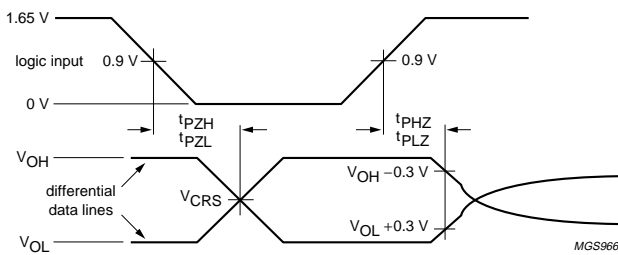


Fig 6. Timing of \overline{OE} to D+ and D-.

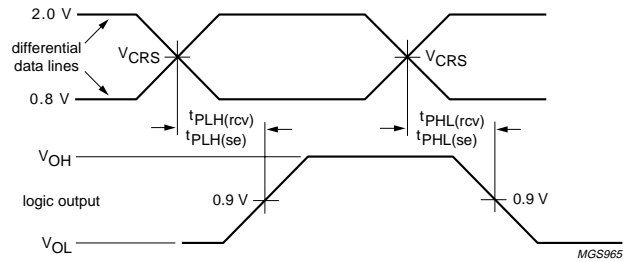
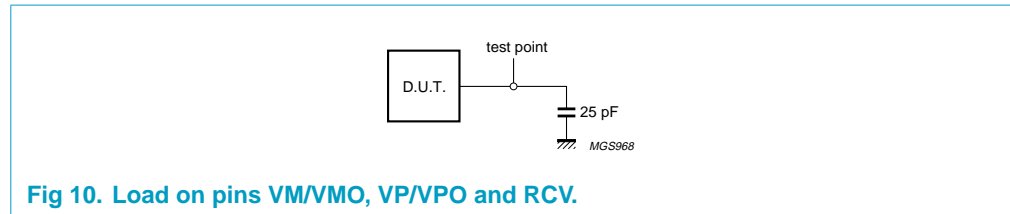
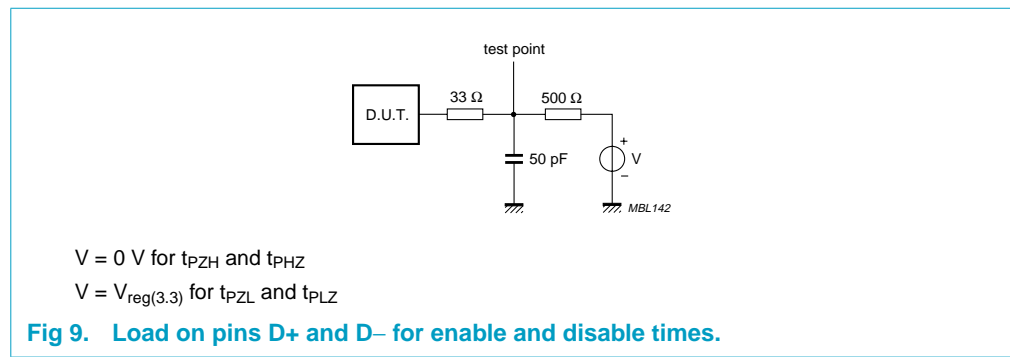
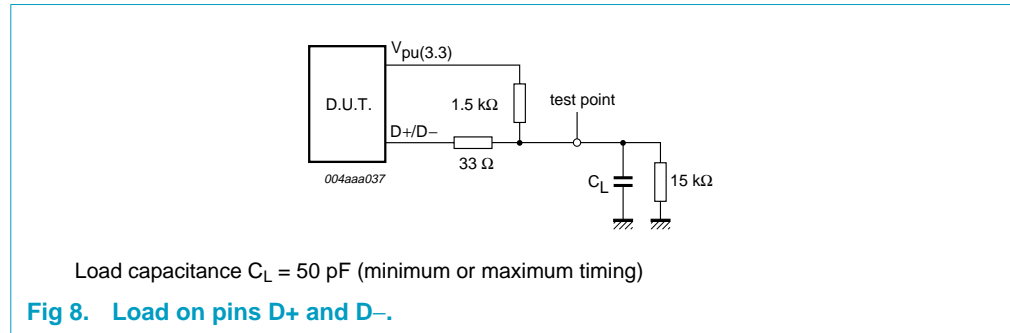


Fig 7. Timing of D+ and D- to RCV, VP/VPO and VM/VMO.

13. Test information



14. Package outline

HBCC16: plastic thermal enhanced bottom chip carrier; 16 terminals; body 3 x 3 x 0.65 mm

SOT639-2

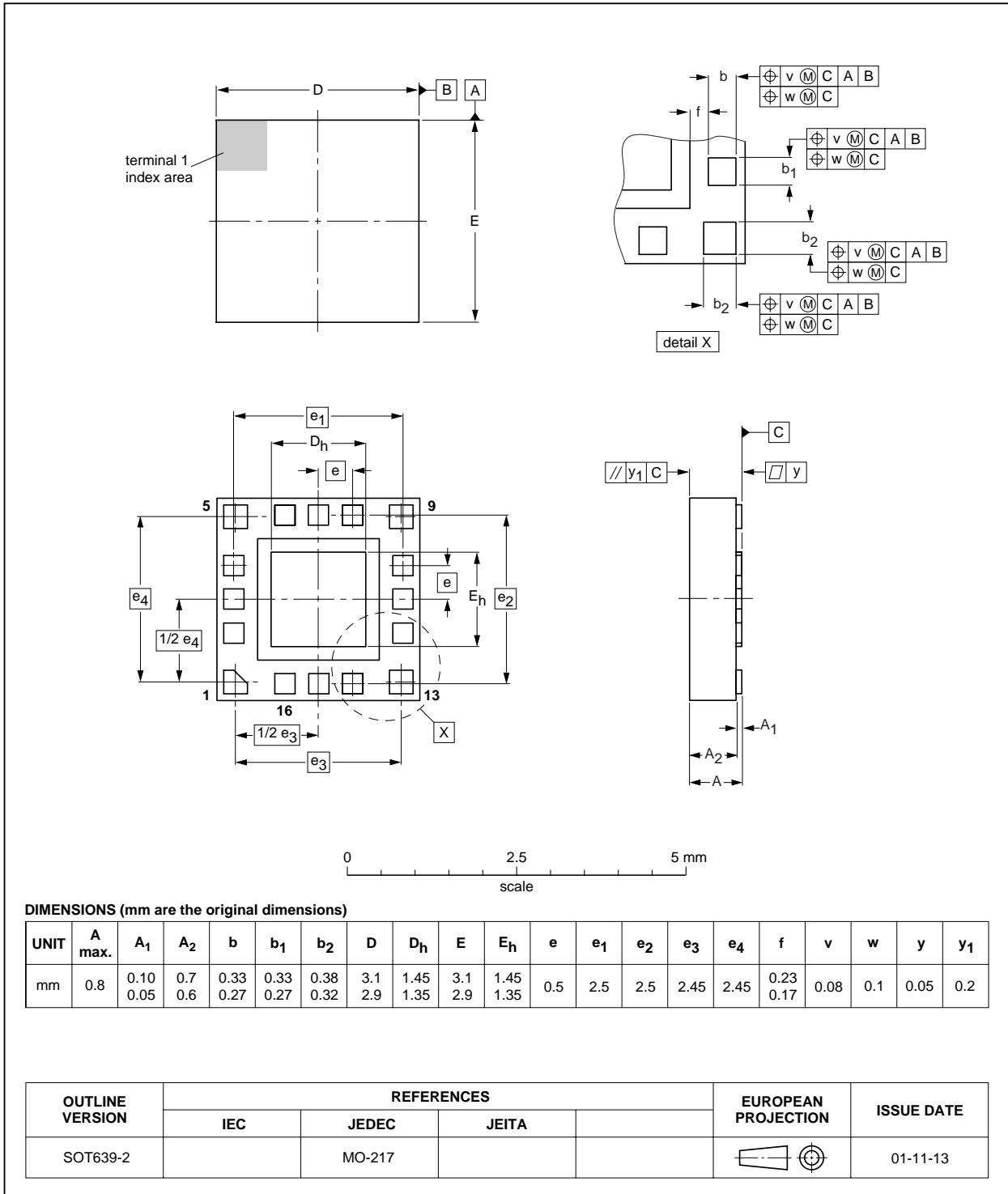


Fig 11. Package outline.

15. Packaging

The ISP1102W (HBCC16 package) is delivered on a Type A carrier tape, see [Figure 12](#). The tape dimensions are given in [Table 15](#).

The reel diameter is 330 mm. The reel is made of polystyrene (PS) and is not designed for use in a baking process.

The cumulative tolerance of 10 successive sprocket holes is ± 0.02 mm. The camber must not exceed 1 mm in 100 mm.

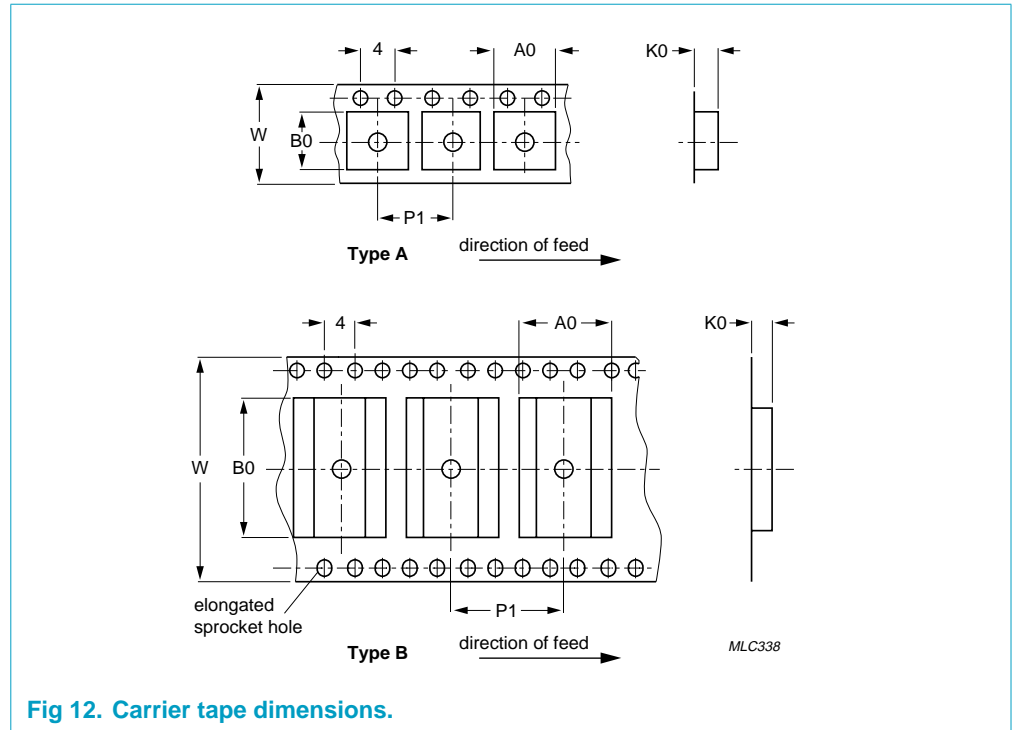


Fig 12. Carrier tape dimensions.

Table 15: Type A carrier tape dimensions for the ISP1102W

Dimension	Value	Unit
A0	3.3	mm
B0	3.3	mm
K0	1.1	mm
P1	8.0	mm
W	12.0 \pm 0.3	mm

16. Soldering

16.1 Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *Data Handbook IC26; Integrated Circuit Packages* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

16.2 Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferably be kept below 220 °C for thick/large packages, and below 235 °C small/thin packages.

16.3 Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

16.4 Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

16.5 Package related soldering information

Table 16: Suitability of surface mount IC packages for wave and reflow soldering methods

Package ^[1]	Soldering method	
	Wave	Reflow ^[2]
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable
DHVQFN, HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ^[3]	suitable
PLCC ^[4] , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ^{[4][5]}	suitable
SSOP, TSSOP, VSO	not recommended ^[6]	suitable

[1] For more detailed information on the BGA packages refer to the *(LF)BGA Application Note* (AN01026); order a copy from your Philips Semiconductors sales office.

[2] All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods*.

[3] These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.

[4] If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.

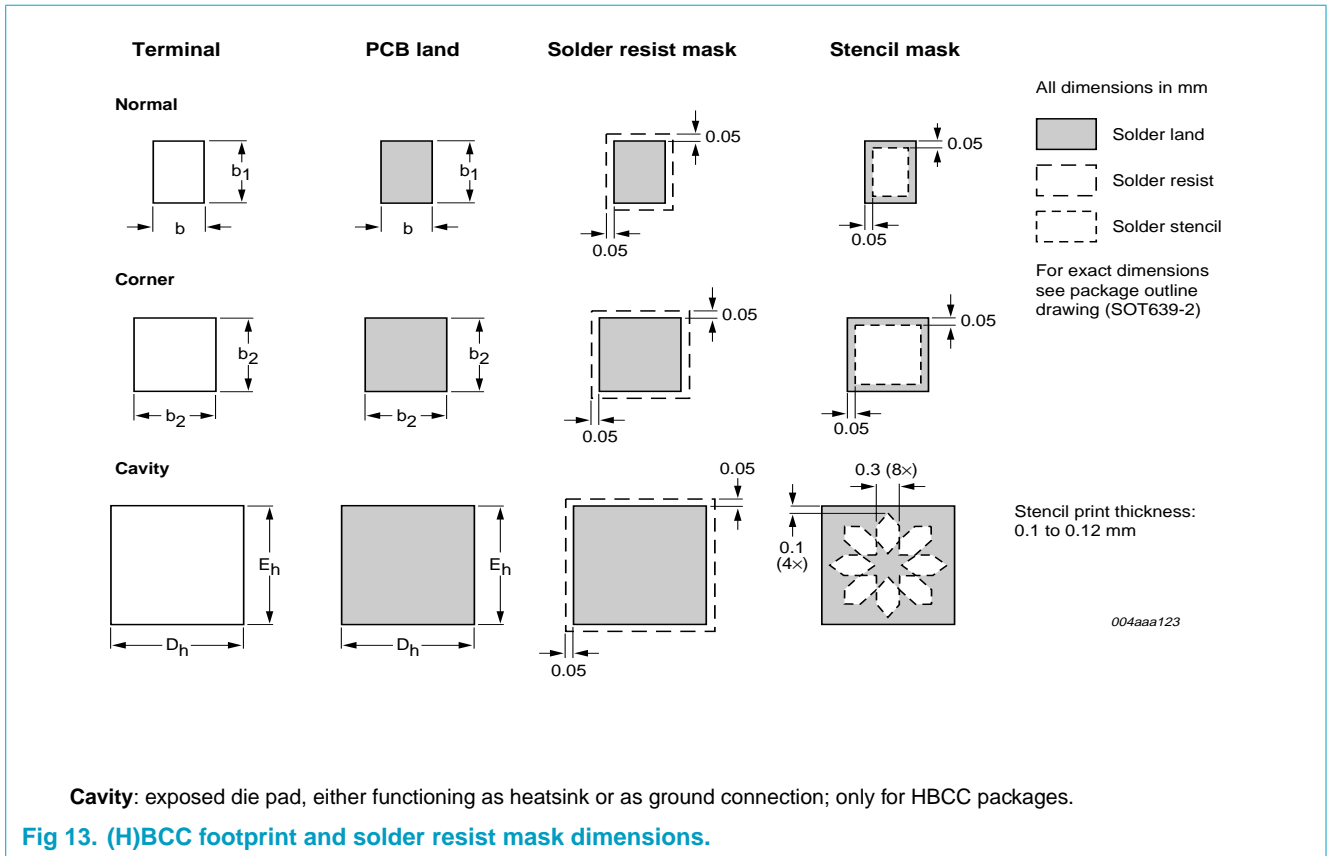
[5] Wave soldering is suitable for LQFP, QFP and TQFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.

[6] Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

17. Additional soldering information

17.1 (H)BCC packages: footprint

The surface material of the terminals on the resin protrusion consists of a 4-layer metal structure (Au, Pd, Ni and Pd). The Au + Pd layer (0.1 μm minimum) ensures solderability, the Ni layer (5 μm minimum) prevents diffusion, and the Pd layer on top (0.5 μm minimum) ensures effective wire bonding.



17.2 (H)BCC packages: reflow soldering profile

The conditions for reflow soldering of (H)BCC packages are as follows:

- **Preheating time:**
 - minimum 90 s at $T = 145$ to 155 °C.
- **Soldering time:**
 - BCC package minimum 90 s at $T > 183$ °C
 - HBCC package minimum 100 s at $T > 183$ °C.
- **Peak temperature:**
 - Ambient temperature: $T_{amb(max)} = 260$ °C
 - Device surface temperature: $T_{case(max)} = 255$ °C.

18. Revision history

Table 17: Revision history

Rev	Date	CPCN	Description
02	20030106	-	Product data (9397 750 10397) Modifications: <ul style="list-style-type: none">• text updated
01	20000524	-	Objective data.

19. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Contents

1	General description	1
2	Features	1
3	Applications	2
4	Ordering information	2
5	Block diagram	2
6	Pinning information	3
6.1	Pinning	3
6.2	Pin description	3
7	Functional description	5
7.1	Function selection	5
7.2	Operating functions	5
7.3	Power supply configurations	5
7.4	Power supply input options	7
8	Electrostatic discharge (ESD)	8
8.1	ESD protection	8
8.2	ESD test conditions	8
9	Limiting values	9
10	Recommended operating conditions	9
11	Static characteristics	9
12	Dynamic characteristics	12
13	Test information	15
14	Package outline	16
15	Packaging	17
16	Soldering	18
16.1	Introduction to soldering surface mount packages	18
16.2	Reflow soldering	18
16.3	Wave soldering	18
16.4	Manual soldering	19
16.5	Package related soldering information	19
17	Additional soldering information	20
17.1	(H)BCC packages: footprint	20
17.2	(H)BCC packages: reflow soldering profile	20
18	Revision history	21
19	Data sheet status	22
20	Definitions	22
21	Disclaimers	22



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